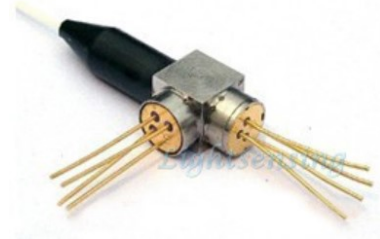


Double wavelength laser diode Version: 3.1.1 17-09-01

Model: LSLD

Features:

- 850/1310/1490/1550nm MQW DFB or FP LD Available
- Single mode or multimode
- Good high temperature characteristic, High reliable
- High side-mode-suppression ratio (typical>35dB)
- Built-in monitor PD
- Low threshold/operate current
- Metal can type hermetic, Compact size



Applications:

- Optical Sensing
- Light source
- Test and Measurement Equipment
- Science analysis and experiment

Absolute maximum ratings:

parameter	symbol	value	unit
Operating temperature	Top	-40~+85(-10~+60 for 850nm FP)	°C
Storage temperature	Tstg	-40~+100	°C
Laser diode Reverse voltage	V _r	2	V
Soldering temperature/time		260/10	°C/S

DFB LD electrical and optical characteristics:(T=25°C)

parameter	symbol	Min.	Typ.	Max.	unit
Center wavelength	λ	1290	1310	1330	nm
Center wavelength	λ	1480	1490	1500	nm
Center wavelength	λ	1530	1550	1570	nm
Threshold Current	I _{th}		10	15	mA
Operating Current	I _{op}		35	40	mA
Operating Voltage	V _{op}		1.2	1.5	V
Output power(from fiber)	P		2		mW
Spectral width	$\Delta\lambda$		0.3	1	nm
Wavelength/Temp. Coefficient	$\Delta\lambda/\Delta T$		0.1		nm/°C
Side mode suppression ratio	SMSR	35	40		dB
Rise/ Fall time	T _r /T _f (I _{th} +20mA)		0.3	0.7	ns
Monitoring Output Current	I _m (I _{th} +20mA)		0.7		mA
Monitor Dark current	I _d (V _r =5V)			100	nA
Monitor Capacitance	C (V _r =5V)		10		pF
Optical Isolation(note1)	Iso	30			dB Single
		50			dB Double

Note1: temperature range:-20~70°C

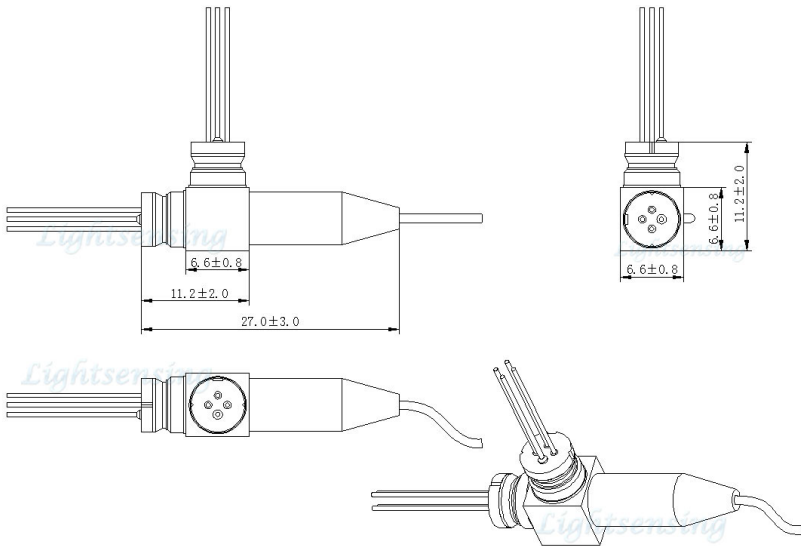
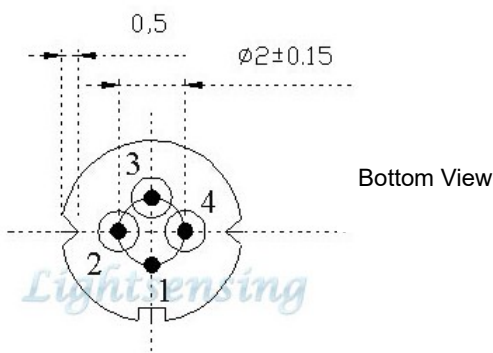
NOTICE: The above product specifications are subject to change without notice.

FP LD electrical and optical characteristics:(T=25°C)

parameter	symbol	Min.	Typ.	Max.	unit
Center wavelength	λ	830	850	870	nm
Center wavelength	λ	1290	1310	1330	nm
Center wavelength	λ	1530	1550	1570	nm
Threshold Current	I _{th}		10	15	mA
Operating Current(850nm FP)	I _{op}		30	35	mA
Operating Current(1310/1550nm FP)	I _{op}		35	40	mA
Operating Voltage(850nm FP)	V _{op}		1.9	2.5	V
Operating Voltage(1310/1550nm FP)	V _{op}		1.2	1.5	V
Output power(from fiber)	P		2		mW
Spectral width	$\Delta\lambda$		3		nm
Rise/ Fall time	Tr/Tf(I _{th} +20mA)		1		ns
Monitoring Output Current	I _m (I _{th} +20mA)		1		mA
Monitor Dark current	I _d (V _r =5V)			100	nA
Monitor Capacitance	C (V _r =5V)		10		pF
Optical Isolation(note1)	Iso	30			dB Single
		50			dB Double

Note1: temperature range:-20~70°C

NOTICE: The above product specifications are subject to change without notice.

The package Dimensions

PIN description and PIN OUT for 1310/1490/1550nm DFB or FP


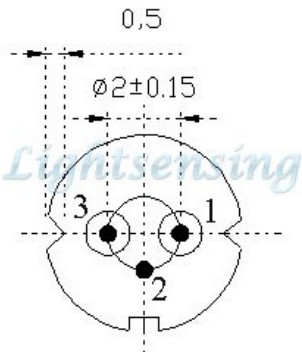
	F type	S type
1	LD(+)/case	case
2	LD(-)	LD(-)
3	PD(-)	PD(+)
4	PD(+)	LD(+)/PD(-)

地址：北京市海淀区苏州街 12 号西屋国际 E 座 1201 邮编：100080

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 TEL: +86-010-82873449 FAX: +86-010-62557230 Email: info@lightsensing.com Website: www.lightsensing.com

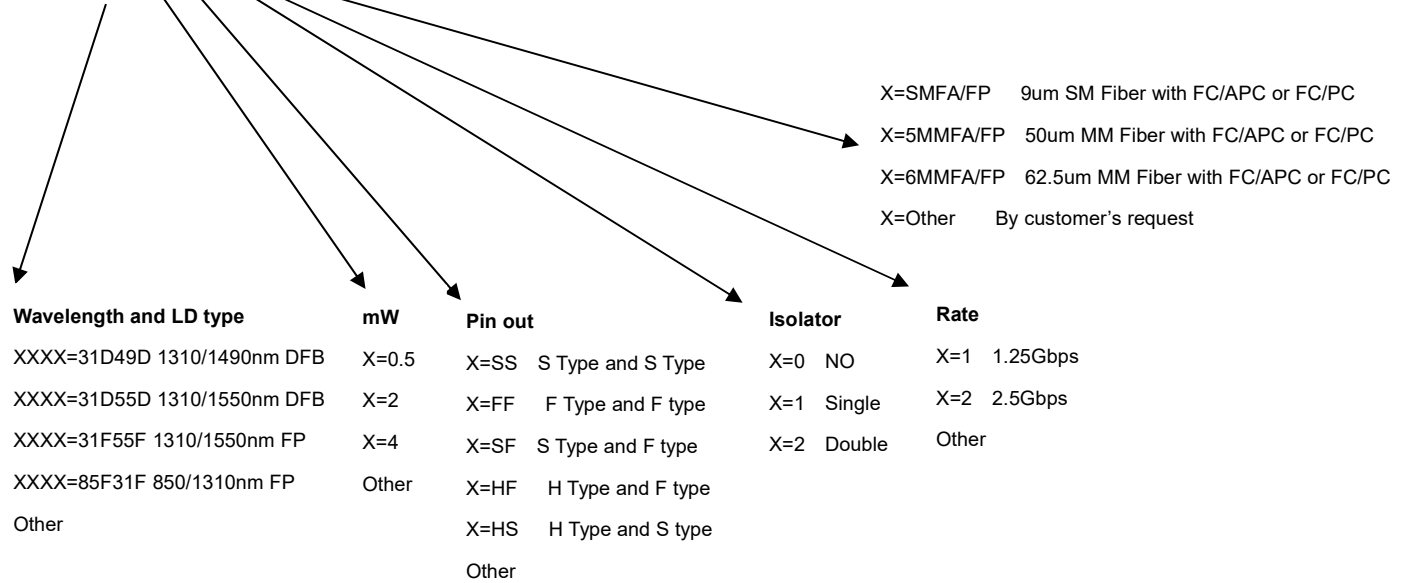
PIN description and PIN OUT for 850nm FP



H Type	
1	LD Cathode
2	LD anode, PD cathode, case
3	PD anode

Order information

LSLD-XXX-X-XX-X-X-X



X=SMFA/FP 9um SM Fiber with FC/APC or FC/PC
 X=5MMFA/FP 50um MM Fiber with FC/APC or FC/PC
 X=6MMFA/FP 62.5um MM Fiber with FC/APC or FC/PC
 X=Other By customer's request

Wavelength and LD type	mW	Pin out	Isolator	Rate
XXXX=31D49D 1310/1490nm DFB	X=0.5	X=SS S Type and S Type	X=0 NO	X=1 1.25Gbps
XXXX=31D55D 1310/1550nm DFB	X=2	X=FF F Type and F type	X=1 Single	X=2 2.5Gbps
XXXX=31F55F 1310/1550nm FP	X=4	X=SF S Type and F type	X=2 Double	Other
XXXX=85F31F 850/1310nm FP	Other	X=HF H Type and F type		
Other		X=HS H Type and S type		
		Other		

The cautions

- 1: The suitable ESD protection is required in storage, transportation and using
- 2: The fiber bending radius no less than 20mm for avoiding fiber damaged ,Be sure the fiber coupling facet is clean before connecting it to opto-circuit.